

MDF8N60B-VB Datasheet

N-Channel 600V (D-S) Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	600	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$	0.88
Q_g max. (nC)	49	
Q_{gs} (nC)	13	
Q_{gd} (nC)	20	
Configuration	Single	

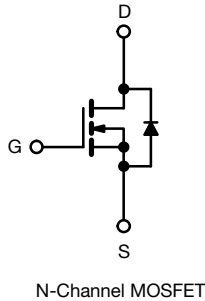
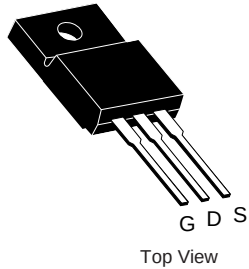
FEATURES

- Low gate charge Q_g results in simple drive requirement
- Improved gate, avalanche and dynamic dV/dt ruggedness
- Fully characterized capacitance and avalanche voltage and current



Available
RoHS*
Available

TO-220 FULLPAK



APPLICATIONS

- Switch mode power supply (SMPS)
- Uninterruptible power supply
- High speed power switching

APPLICABLE OFF LINE SMPS TOPOLOGIES

- Active clamped forward
- Main switch

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V _{DS}	600	V
Gate-Source Voltage			V _{GS}	± 30	
Continuous Drain Current	V _{GS} at 10 V	T _C = 25 °C	I _D	8.0	A
		T _C = 100 °C		5.8	
Pulsed Drain Current ^a			I _{DM}	37	
Linear Derating Factor				1.3	W/°C
Single Pulse Avalanche Energy ^b			E _{AS}	290	mJ
Repetitive Avalanche Current ^a			I _{AR}	8.0	A
Repetitive Avalanche Energy ^a			E _{AR}	17	mJ
Maximum Power Dissipation	T _C = 25 °C		P _D	37	W
Peak Diode Recovery dV/dt ^c			dV/dt	5.0	V/ns
Operating Junction and Storage Temperature Range			T _J , T _{stg}	-55 to +150	°C
Soldering Recommendations (Peak temperature) ^d		for 10 s		300	
Mounting Torque	6-32 or M3 screw			10	lbf · in
				1.1	N · m

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting $T_J = 25\text{ }^\circ\text{C}$, $L = 6.8\text{ mH}$, $R_g = 25\text{ }\Omega$, $I_{AS} = 9.2\text{ A}$ (see fig. 12).
- $I_{SD} \leq 9.2\text{ A}$, $dI/dt \leq 50\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^\circ\text{C}$.
- 1.6 mm from case.

THERMAL RESISTANCE RATINGS

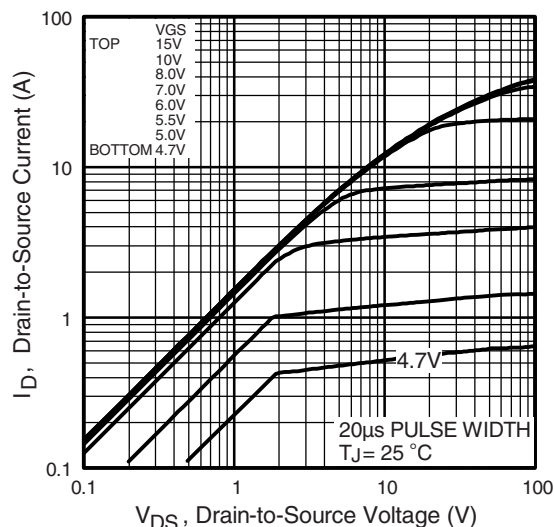
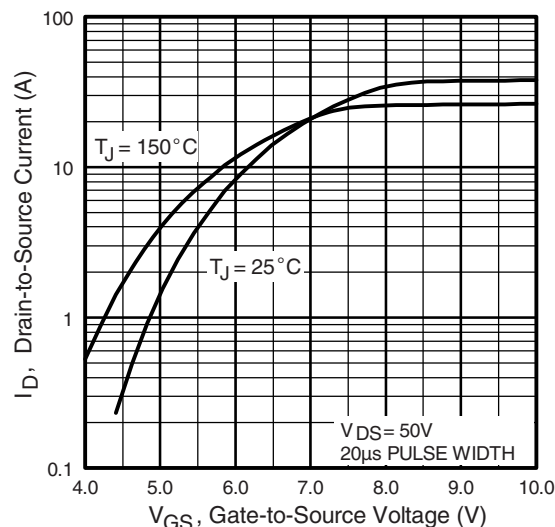
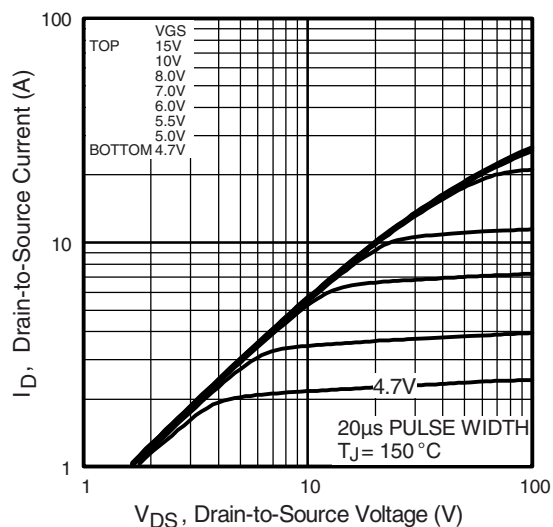
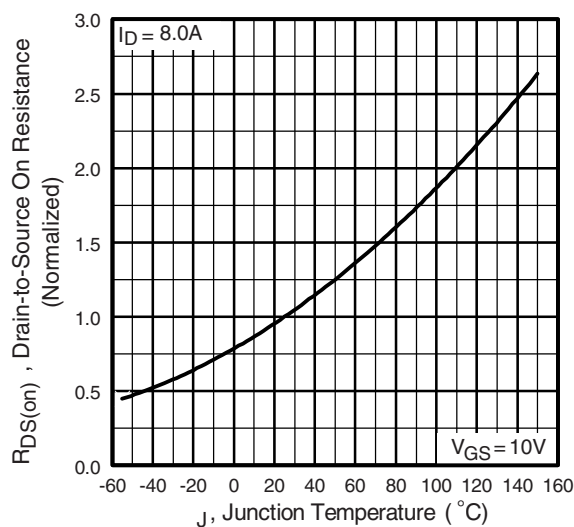
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.50	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.75	

SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	600	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^{\circ}\text{C}$, $I_D = 1\text{ mA}$	-	660	-	mV/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 600\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	25	μA
		$V_{DS} = 480\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 5.5\text{ A}^b$	-	0.88	-	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}$, $I_D = 5.5\text{ A}$	5.5	-	-	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1.0\text{ MHz}$, see fig. 5	-	890	-	pF
Output Capacitance	C_{oss}		-	180	-	
Reverse Transfer Capacitance	C_{rss}		-	7.1	-	
Output Capacitance	C_{oss}	$V_{GS} = 0\text{ V}$ $V_{DS} = 1.0\text{ V}$, $f = 1.0\text{ MHz}$ $V_{DS} = 480\text{ V}$, $f = 1.0\text{ MHz}$	-	1957	-	
Effective Output Capacitance	$C_{oss\text{ eff.}}$		-	49	-	
		$V_{DS} = 0\text{ V to } 480\text{ V}$	-	96	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$ $I_D = 8.0\text{ A}$, $V_{DS} = 400\text{ V}$ see fig. 6 and 13 ^b	-	-	49	nC
Gate-Source Charge	Q_{gs}		-	-	13	
Gate-Drain Charge	Q_{gd}		-	-	20	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 300\text{ V}$, $I_D = 8.0\text{ A}$ $R_g = 9.1\text{ }\Omega$, $R_D = 35.5\text{ }\Omega$, see fig. 10 ^b	-	13	-	ns
Rise Time	t_r		-	25	-	
Turn-Off Delay Time	$t_{d(off)}$		-	30	-	
Fall Time	t_f		-	22	-	
Gate Input Resistance	R_g	$f = 1\text{ MHz}$, open drain	0.5	-	3.2	Ω
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	9.2	A
Pulsed Diode Forward Current ^a	I_{SM}		-	-	37	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_S = 8.0\text{ A}$, $V_{GS} = 0\text{ V}^b$	-	-	1.5	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_F = 8.0\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}^b$	-	530	800	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	3.0	4.4	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
 b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.
 c. $C_{oss\text{ eff.}}$ effective is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

Fig. 3 - Typical Transfer Characteristics

Fig. 2 - Typical Output Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

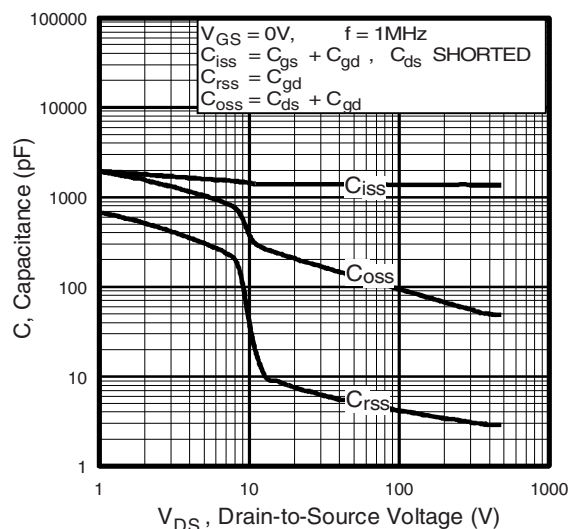


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

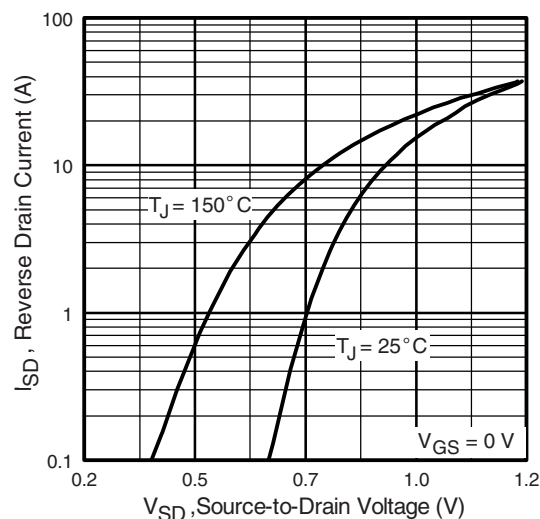


Fig. 7 - Typical Source-Drain Diode Forward Voltage

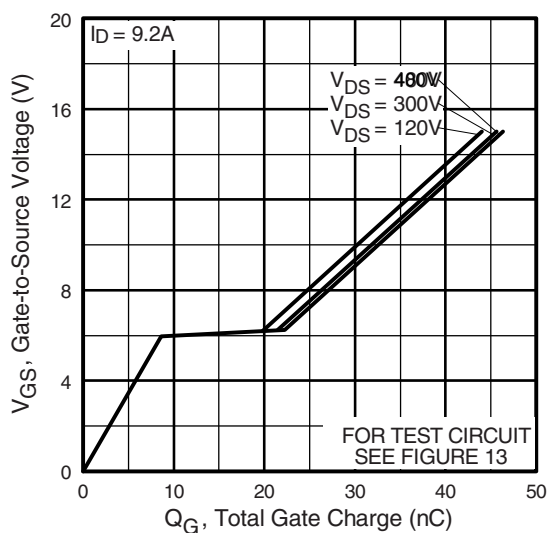


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

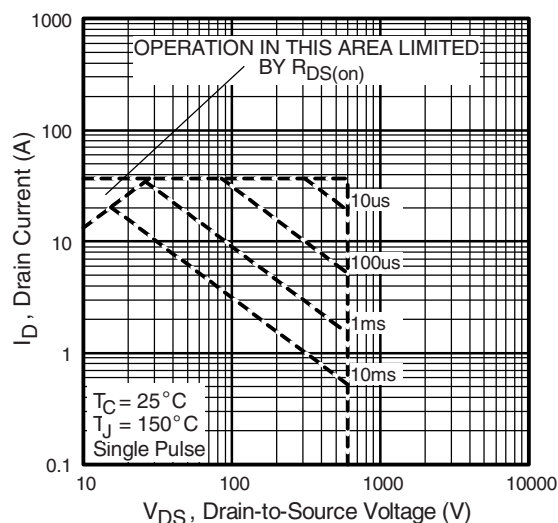


Fig. 8 - Maximum Safe Operating Area

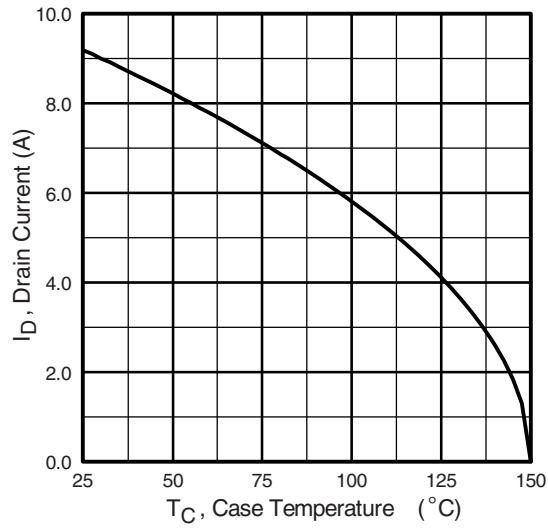


Fig. 9 - Maximum Drain Current vs. Case Temperature

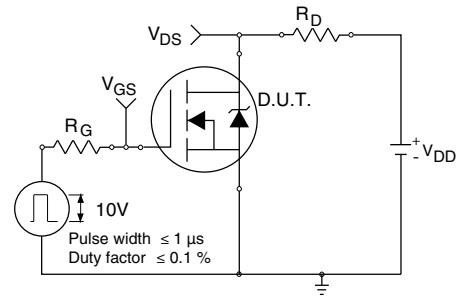


Fig. 10a - Switching Time Test Circuit

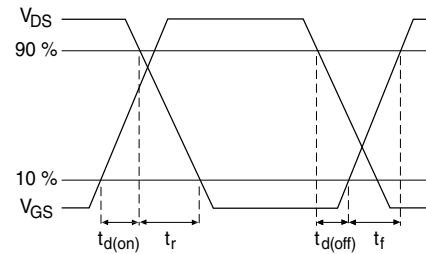


Fig. 10b - Switching Time Waveforms

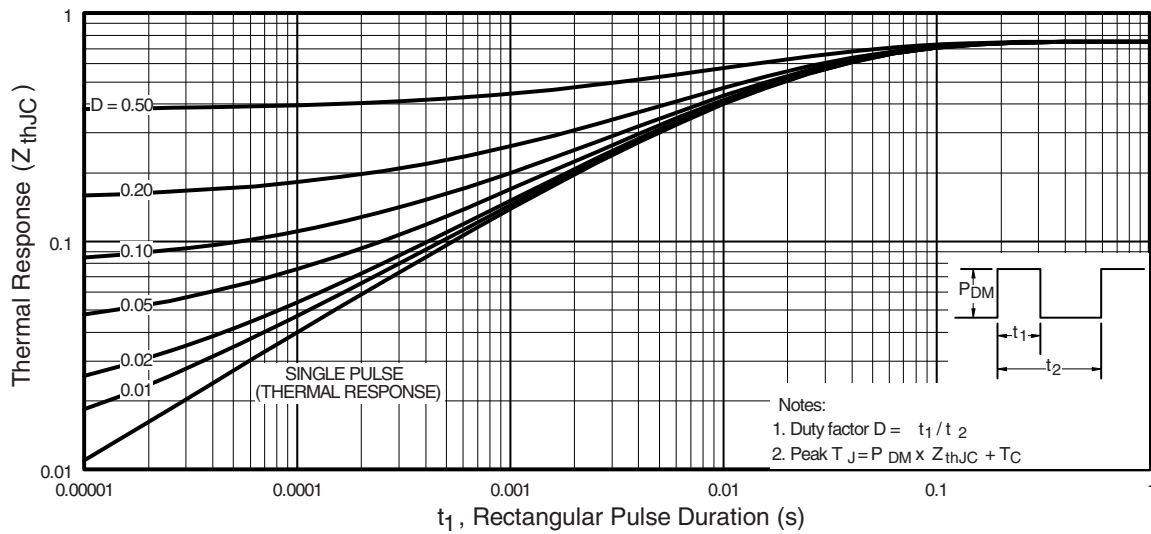


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

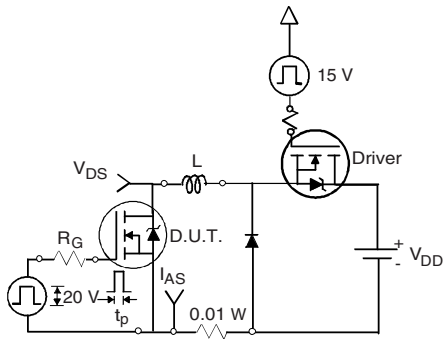


Fig. 12a - Unclamped Inductive Test Circuit

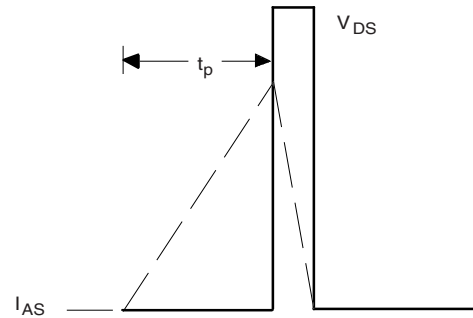


Fig. 12b - Unclamped Inductive Waveforms

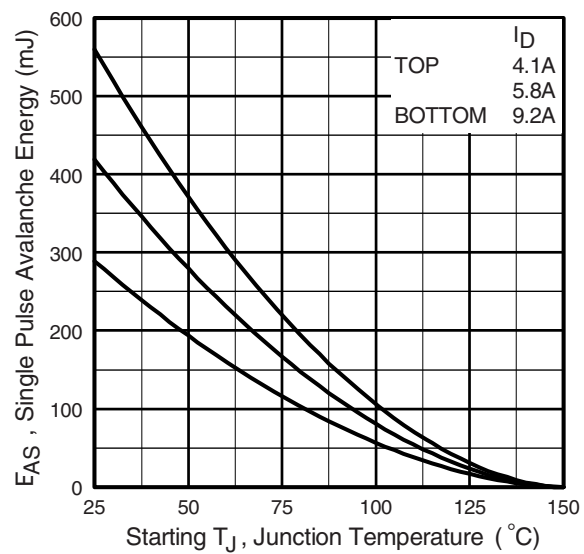


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

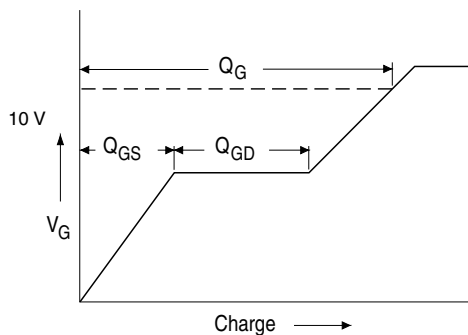


Fig. 13a - Basic Gate Charge Waveform

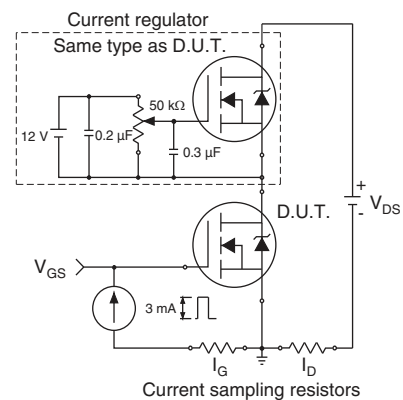
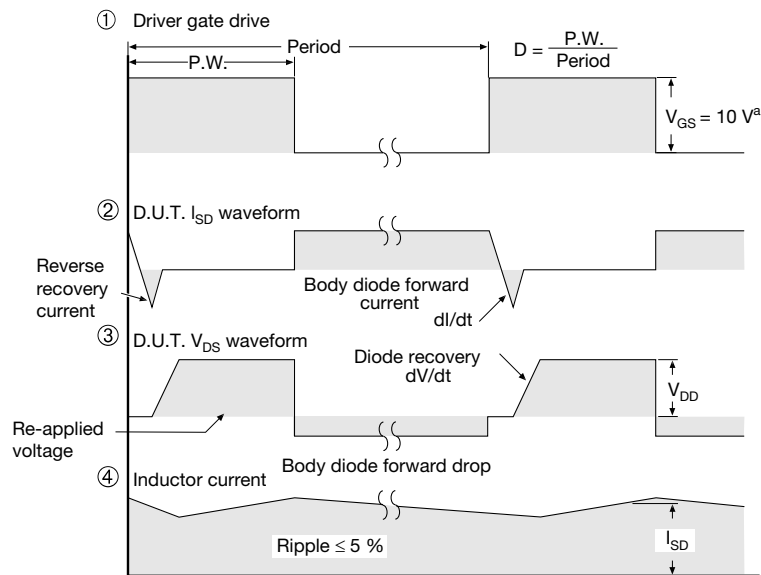
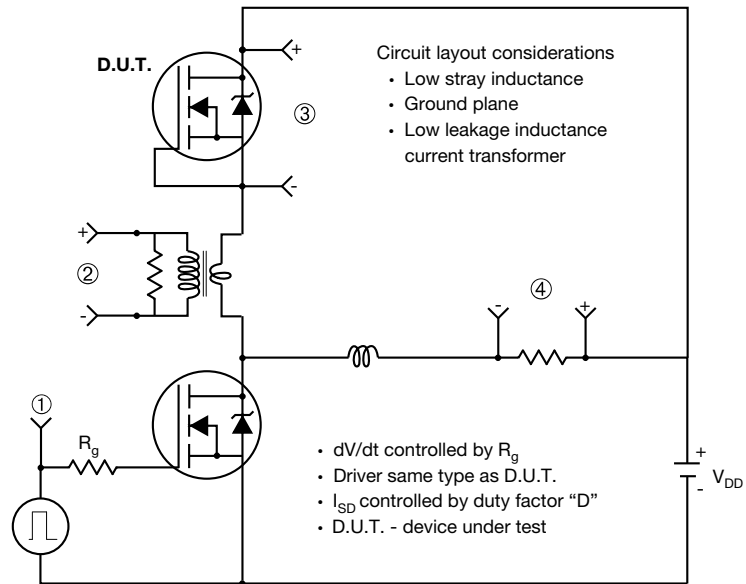


Fig. 13b - Gate Charge Test Circuit

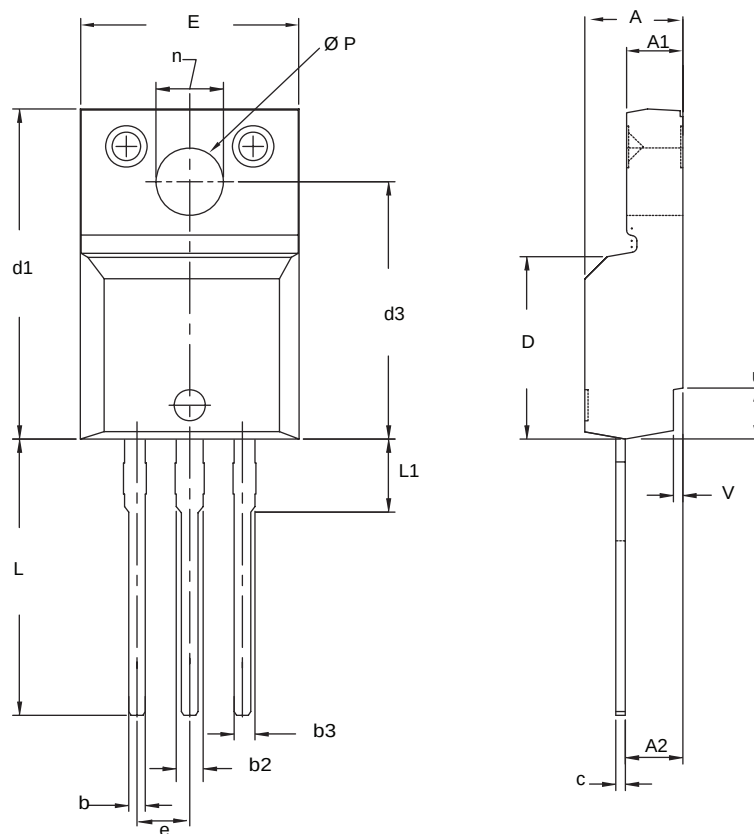
Peak Diode Recovery dV/dt Test Circuit



Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

TO-220 FULLPAK (HIGH VOLTAGE)

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.570	4.830	0.180	0.190
A1	2.570	2.830	0.101	0.111
A2	2.510	2.850	0.099	0.112
b	0.622	0.890	0.024	0.035
b2	1.229	1.400	0.048	0.055
b3	1.229	1.400	0.048	0.055
c	0.440	0.629	0.017	0.025
D	8.650	9.800	0.341	0.386
d1	15.88	16.120	0.622	0.635
d3	12.300	12.920	0.484	0.509
E	10.360	10.630	0.408	0.419
e	2.54 BSC		0.100 BSC	
L	13.200	13.730	0.520	0.541
L1	3.100	3.500	0.122	0.138
n	6.050	6.150	0.238	0.242
Ø P	3.050	3.450	0.120	0.136
u	2.400	2.500	0.094	0.098
v	0.400	0.500	0.016	0.020

ECN: X09-0126-Rev. B, 26-Oct-09
DWG: 5972

Notes

1. To be used only for process drawing.
2. These dimensions apply to all TO-220, FULLPAK leadframe versions 3 leads.
3. All critical dimensions should C meet $C_{pk} > 1.33$.
4. All dimensions include burrs and plating thickness.
5. No chipping or package damage.

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